

(b) Amendments to the Claims:

Please amend claim 17 as follows. A detailed listing of the claims is provided.

1. - 16. (Cancelled).

17. (Currently Amended) An accumulated film forming apparatus for continuously accumulating a plurality of semiconductor layers on a long substrate by the plasma CVD method, characterized by at least a first accumulation chamber for making an i-type layer having means for making raw material gas flow from the upper part toward the lower part in the direction of movement of said long substrate, and a second accumulation chamber for making a p-type layer on said i-type layer having means for making the raw material gas containing a p-type dopant flow from the lower part toward the upper part in the direction of movement of said long substrate, said first accumulation chamber and said second accumulation chamber being connected together by a separating path, said separating path being a gas gate to prevent diffusion of said gas containing said p-type dopant in said second accumulation chamber from diffusing into the first accumulation chamber.

18. (Original) An accumulated film forming apparatus according to claim 17, characterized in that the area of an electrode in at least said second accumulation chamber for applying electric power for causing plasma is larger than the area of said long substrate in said accumulation chamber.

19. (Original) An accumulated film forming apparatus according to claim 18, characterized in that said electrode is fin-shaped.

20. (Original) An accumulated film forming apparatus according to claim 18, characterized in that said electrode is enclosure-shaped.

21. (Original) An accumulated film forming apparatus according to claim 18, characterized in that the potential of said electrode is positive relative to said long substrate.

22. (Original) An accumulated film forming apparatus according to claim 17, characterized in that a portion for supplying said raw material gas into said accumulation chambers has a member for shielding said long substrate from the flow of said raw material gas.

23. - 27. (Cancelled).